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(71) Applicant (*for all designated States except US*): **MATT-
SON THERMAL PRODUCTS GMBH** [DE/DE]; Daim-
lerstrasse 10, 89160 Dornstadt (DE).

(72) Inventors; and

(75) Inventors/Applicants (*for US only*): **NENYEI, Zsolt**
[DE/DE]; Sperberweg 4, 89134 Blaustein (DE). **CHUNG,**
Hin, Yiu [DE/DE]; Stiergartenweg 6, 89275 Elchingen
(DE).

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(54) Title: A PROCESS FOR THE PRODUCTION OF A NITROGENOUS LAYER ON A SEMICONDUCTOR OR METAL
SURFACE

(57) Abstract: A first process for the production of a thin nitrogenous layer on a semiconductor surface by contacting at least a part
of the surface with a nitrogenous liquid, by applying an electrical voltage between the surface, the liquid and an electrode according
to a given voltage-time curve until a layer thickness of less than 5 nm is formed, and then separating the surface from the liquid.
A second process for the production of a thin nitrogenous layer on a metal surface or on a metal layer located on a substrate by
contacting at least a part of the surface or the metal layer with a nitrogenous liquid, by applying an electrical voltage between the
surface or metal layer, the liquid and an electrode according to a given voltage-time curve until a layer thickness of less than 50 nm
is formed, and then separating the surface or the metal layer from the liquid. A third process for detaching an oxygen-containing
and/or nitrogenous layer on a semiconductor or a metal surface.



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